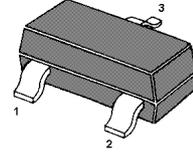


MMBTA05

NPN Silicon Epitaxial Planar Transistor

For switching and amplifier applications



1. Base 2. Emitter 3. Collector
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	60	V
Collector Emitter Voltage	V_{CEO}	60	V
Emitter Base Voltage	V_{EBO}	4	V
Collector Current	I_C	500	mA
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction to Ambient ¹⁾	$R_{\theta JA}$	357	$^\circ\text{C/W}$

¹⁾ Device mounted on FR-4 substrate PC board, with minimum recommended pad layout.

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 1\text{ V}$, $I_C = 10\text{ mA}$	h_{FE}	100	-	-
at $V_{CE} = 1\text{ V}$, $I_C = 100\text{ mA}$	h_{FE}	100	-	-
Collector Base Cutoff Current at $V_{CB} = 60\text{ V}$	I_{CBO}	-	100	nA
Collector Emitter Cutoff Current at $V_{CE} = 60\text{ V}$	I_{CES}	-	100	nA
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CBO}$	60	-	V
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	60	-	V
Emitter Base Breakdown Voltage at $I_E = 100\text{ }\mu\text{A}$	$V_{(BR)EBO}$	4	-	V
Collector Emitter Saturation Voltage at $I_C = 100\text{ mA}$, $I_B = 10\text{ mA}$	$V_{CE(sat)}$	-	0.25	V
Base Emitter On Voltage at $V_{CE} = 1\text{ V}$, $I_C = 100\text{ mA}$	$V_{BE(on)}$	-	1.2	V
Gain Bandwidth Product at $I_C = 10\text{ mA}$, $V_{CE} = 2\text{ V}$, $f = 100\text{ MHz}$	f_T	100	-	MHz

Electrical Characteristics Curves

Fig. 1 Output Characteristics Curve

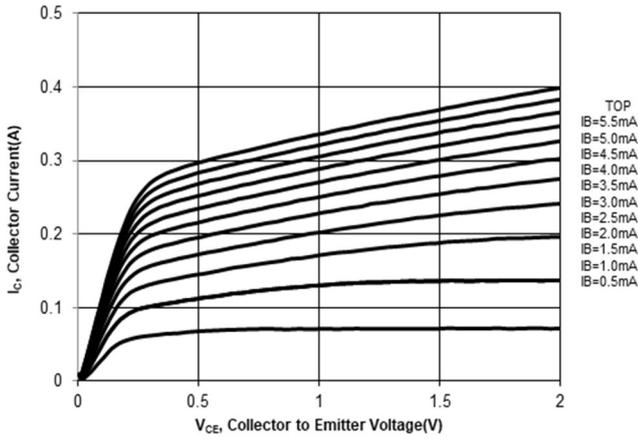


Fig. 2 Output Characteristics Curve

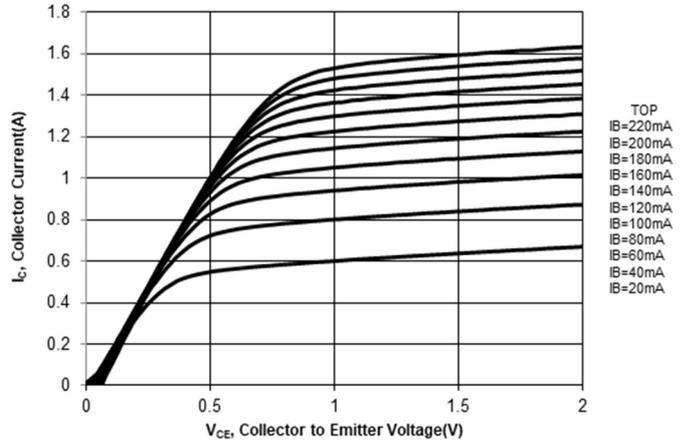


Fig. 3 Collector Current vs. Base-Emitter Voltage

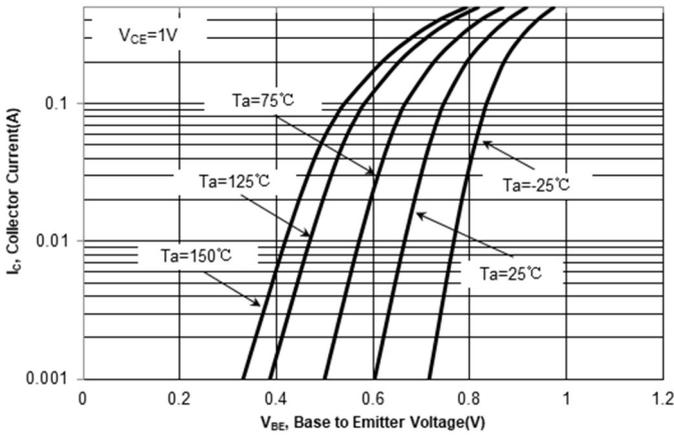
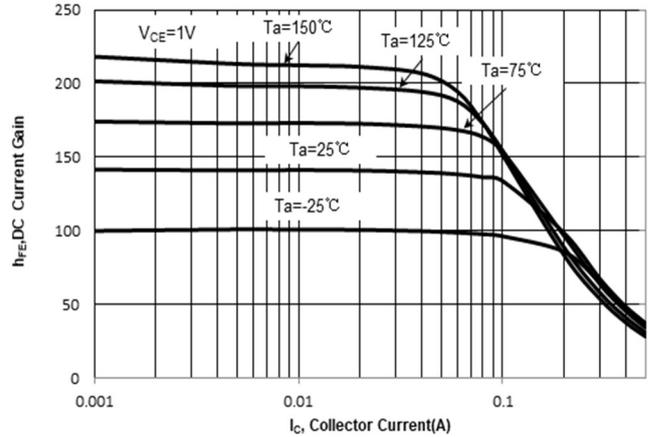


Fig. 4 $h_{FE,DC}$ Current Gain vs. Collector Current



Electrical Characteristics Curves

Fig. 5 $V_{BE(sat)}$ vs. Collector Current

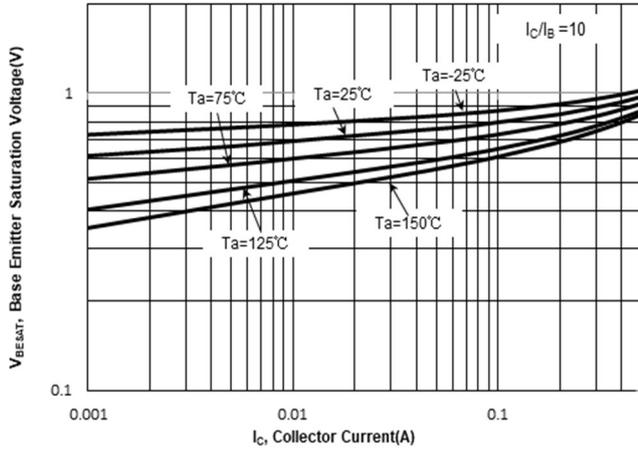


Fig. 6 $V_{CE(sat)}$ vs. Collector Current

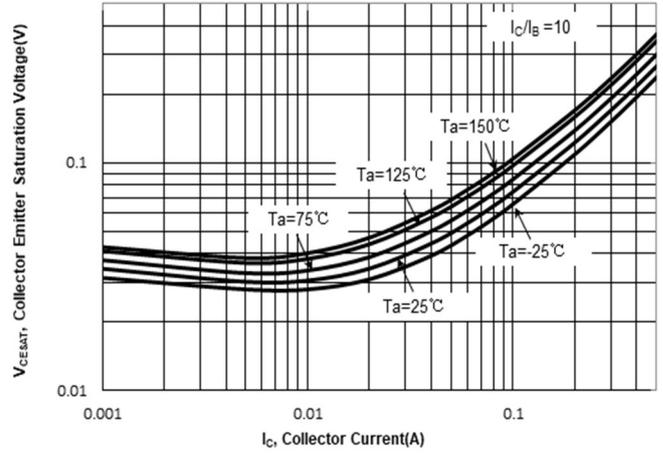


Fig. 7 Capacitance

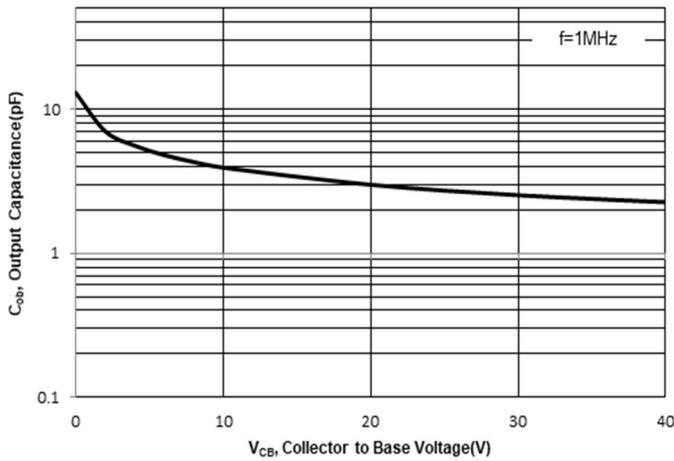


Fig. 8. Power Derating Curve

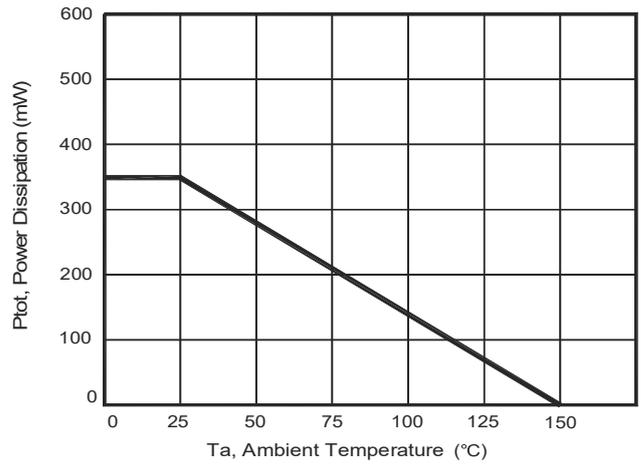
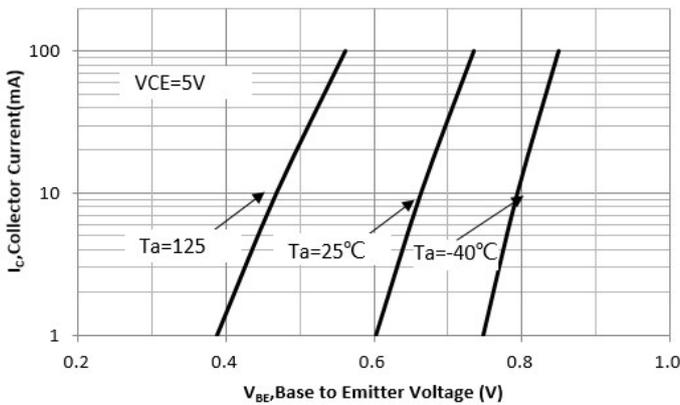
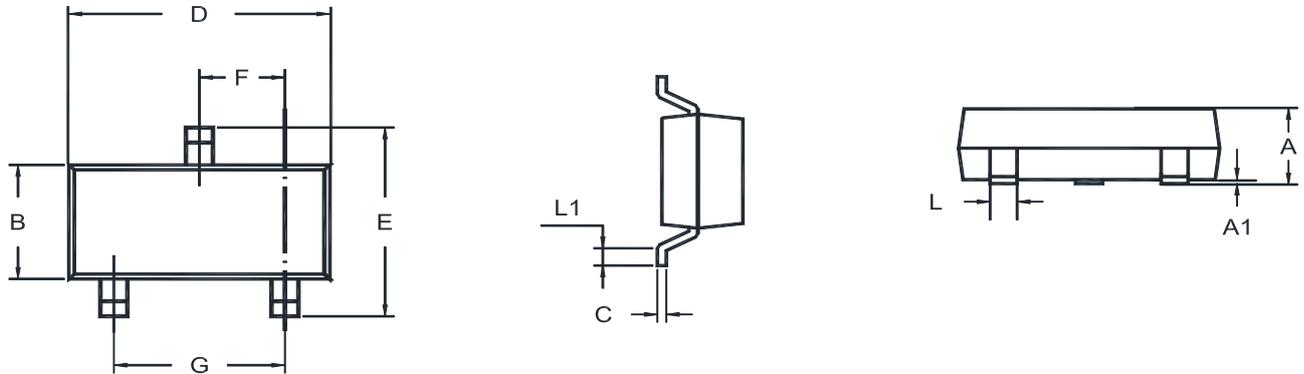


Fig. 9 Collector Current vs. Base-Emitter Voltage



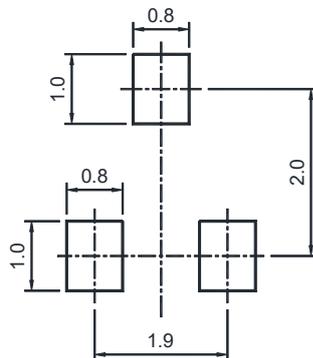
Package Outline (Dimensions in mm)

TO-236



Unit	A	A1	B	C	D	E	F	G	L	L1
mm	1.20	0.100	1.40	0.19	3.04	2.6	1.02	2.04	0.51	0.2
	0.89	0.013	1.20	0.08	2.80	2.2	0.89	1.78	0.37	MIN

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
TO-236	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000

Marking information

"1GM" = Part No.

"YM" = Date Code Marking

"Y" = Year

"M" = Month

Font type: Arial

